

## MB834200B/BL

### CMOS 4M-BIT MASK READ ONLY MEMORY

#### 256K x 16 (512K x 8) CMOS MASK READ ONLY MEMORY

The Fujitsu MB834200B/BL is a CMOS Si-gate mask-programmable static read only memory organized as 262,144 words by 16 bits or 524,288 words by 8 bits.

All pins are TTL-compatible and 3-state output level. The device is full-static operatable (i.e. no need of clock signal) with a single +5V power supply. Also, the MB834200BL can be used with a single +3V power supply which is required for battery powered applications.

The MB834200B/BL is designed for applications such as character generator and program storage which require large memory capacity and high-speed/low-power operation.

The memory organization of MB834200B/BL is configuable between 16 bits and 8 bits by BYTE pin.. (ex. The system using 8 bits CPU and 16 bits CPU can use common data on the same chip.)

- Organization: 262,144 words x 16 bits 524,288 words x 8 bits
- Access time: 150ns max.@Vcc = 5V (MB834200B) 250ns max.@Vcc = 3V (MB834200BL)
- Completely static operation: No clock required
- TTL compatible Input/Output
- Three state output
- Single +5V power supply (MB834200B) Single +3V power supply (MB834200BL)
- Power dissipation: 275mW max. (Active) @Vcc = 5V (MB834200B) 90mW max. (Active) @Vcc = 3V (MB834200BL)
- Standard 40-pin Plastic DIP: Suffix: P
- 48-pin Plastic Thin Small Outline Package (TSOP): Suffix: PFTN(Normal Bend) Suffix: PFTR(Reversed Bend)

#### ABSOLUTE MAXIMUM RATINGS (see NOTE)

Rating	Symbol	Value	Unit
Supply Voltage	Vcc	-0.3 to +7.0 *	٧
Input Voltage	ViN	-0.5 to Vcc +0.5 *	٧
Output Voltage	Vout	-0.5 to Voc +0.5 *	٧
Temperature Under Bias	TBIAS	-10 to +85	°C
Storage Temperature Range	Тѕтс	-45 to +125	°C

#### \* Referenced to GND

Permanent device damage may occur if the above Absolute Maximum Ratings are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



DIP-40P-M01

FPT-48P-M07 See Page 7-16, 7-17 FPT-48P-M08 See Page 7-18, 7-19

PIN ASSIGNMENT

#### ( TOP VIEW ) 40 A8 39 6 Α9 A6 3 A10 **A**5 A11 A<sub>4</sub> 5 A12 Аз A13 **A**2 A14 Αı A15 A٥ 9 A16 CE 10 BYTE Vss | 11 OE | 12 Vss (A-1)/O16 Òв O15 \* **O**7 25 | 1 24 | 1 23 | 1 22 | 1 21 | 1 O14 \* Os ·O<sub>11</sub> 18 O<sub>4</sub> 19 O13 \* $O_5$

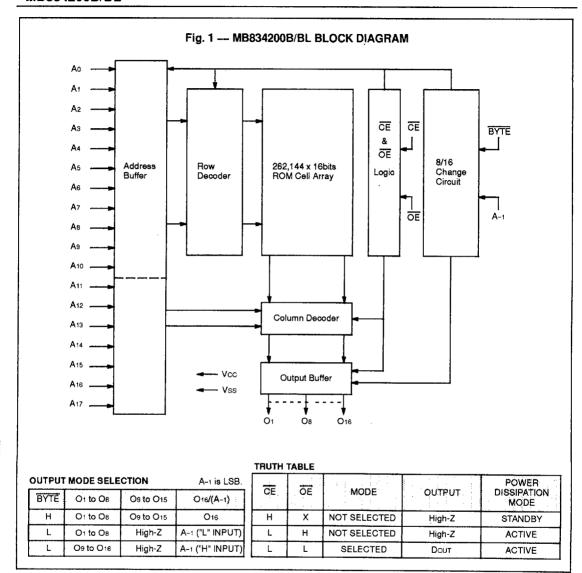
This pin (\*) is High-Z, the device is used 8 bits.

\*O12 🗖 20

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

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Vcc .



# CAPACITANCE (TA=25° C, f=1MHz)

Parameter	Symbol	Min:	Тур	Max	Unit
Output Capacitance (Vout=0V)	Соит		<u> </u>	15	pF
Input Capacitance (ViN=0V)	CIN			10	pF

### **RECOMMENDED OPERATING CONDITIONS**

#### (Referenced to GND)

Parameter	Symbol	MB834200B			MB834200BL			Unit		
		Min	Тур	Max	Min	Тур	Max			
Supply Voltage	Vcc	4.5	5.0	5.5	2.7	3.0	3.6	٧		
Input Low Voltage	VIL	-0.3		0.8	-0.3		0.6	٧		
Input High Voltage	Vін	2.2		Vcc+0.3	Vccx0.7	•	Vcc+0.3	V		
Ambient Temperature	TA	0		70	0		70	°C		

### DC CHARACTERISTICS

#### (Recommended operating conditions unless otherwise noted.)

Parameter	Test Conditions	Symbol	MB834200B			MB834200BL			Unit
			Min	Тур	Max	Min	Тур	Max	
Active Supply Current	CE=VIL, Minimum Cycle Output = Open	lcc			50			25	mA
Standby Supply Current	CE=VIH	İSB1			1			0.5	mA
Standby Supply Surrent	CE=Vcc=ViH, Vin=GND or Vcc	ISB2			10			10	μΑ
Input Leakage Current	Vin=0 to Vcc	lu	-10		10	-5		5	μΑ
Output Leakage Current	CE=VIH, OE=VIH	llvo	-10		10	-5		5	μΑ
Output High Voltage	юн=−400μА	Vон	2.4			2			V
Output Low Voltage	IOL=2.1mA	Vol			0.4			0.4	٧

### Fig. 2 --- AC TEST CONDITIONS

Timing Reference Levels

: 0.6 to 2.4V @Vcc = 5V (MB834200B)

0.4 to Vccx0.8V @Vcc = 3V(MB834200BL)

Input Pulse Rise and Fall Time

: t⊺=5ns

Input Pulse Level

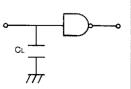
: Input:  $V_{IL}=0.8V$ ,  $V_{IH}=2.2V$  / Output:  $V_{OL}=0.8V$ ,  $V_{OH}=2.2V$ 

@Vcc = 5V (MB834200B)

: Input: VIL=0.6V, VIH=Vccx0.7V / Output: VoL=VoH=1.5V

@Vcc = 3V (MB834200BL)

Output Load : 1 TTL Gate and 100pF



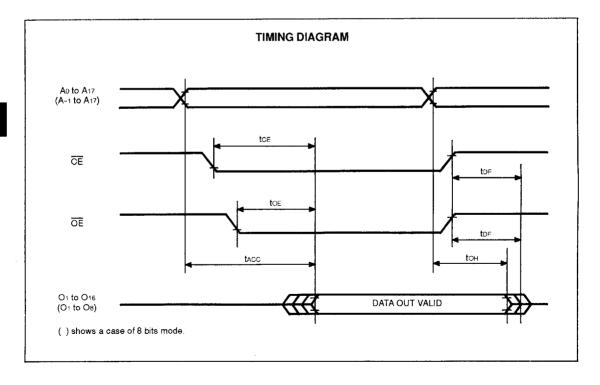
### (Recommended operating conditions unless otherwise noted.)

Parameter	Test Conditions	Symbol	MB83	4200B	MB834	Unit	
			Min	Max	Min	Max	One
Address Access Time	CE=OE=VIL	tacc		150		250	ns
Chip Enable Access Time	ŌË=VIL	tce		150		250	ns
Output Enable Access Time	Note 1	toe		70		200	ns
Output Disable Time	Note 2	tor		60		80	ns
Output Hold Time	CE=OE=VIL	tон	0		0		ns

Note 1: When contineously switching between 3V operation and 5V operation, during Vcc transition the CE should be High state

(Standby mode).

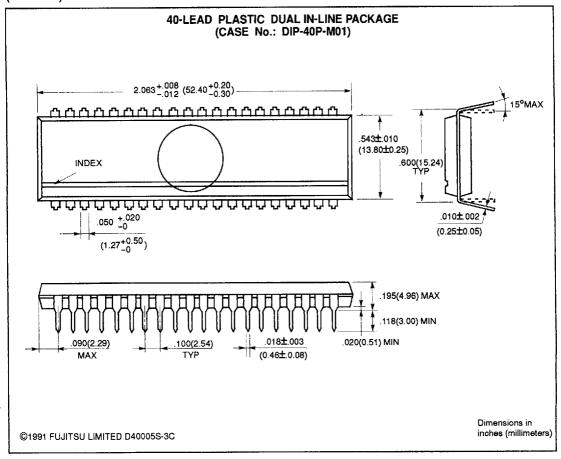
Note 2 : tor is specified by either of CE or OE changing to High earlier.



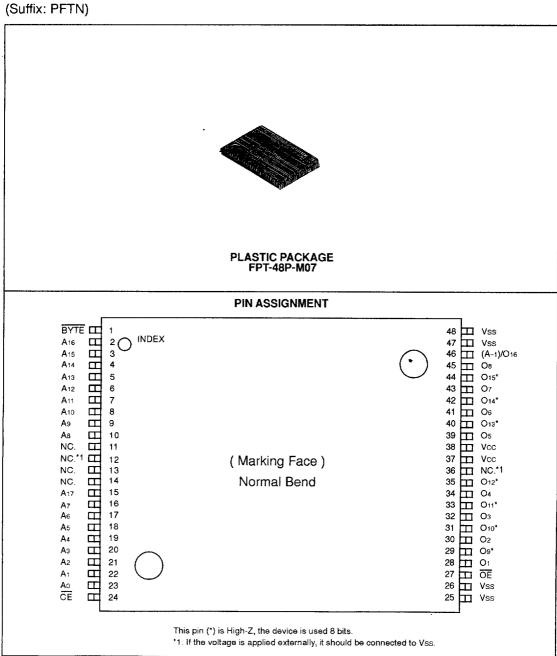
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### PACKAGE DIMENSIONS

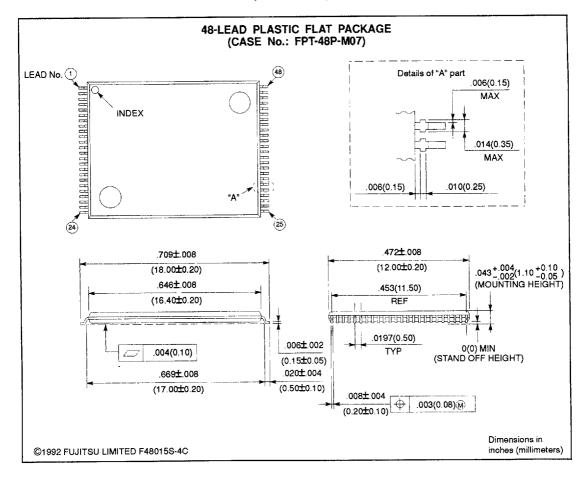
(Suffix: P)



## PACKAGE DIMENSIONS (Continued)

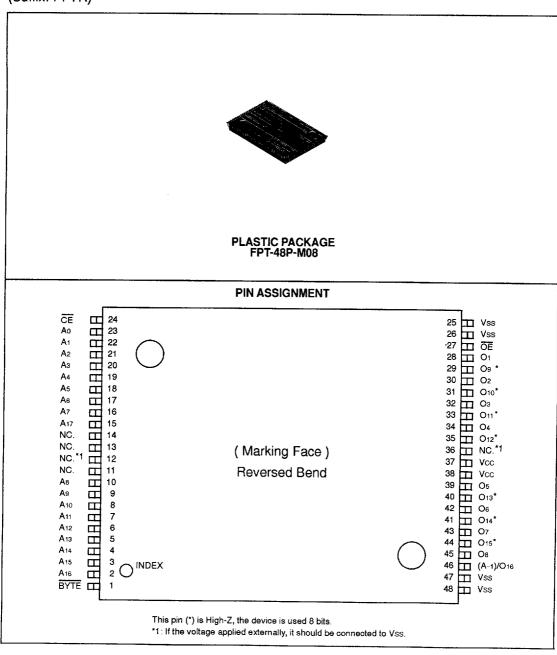


## PACKAGE DIMENSIONS (Continued)



# PACKAGE DIMENSIONS (Continued)

(Suffix: PFTR)



## **PACKAGE DIMENSIONS**

